## SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for rectifying small power applications

## Features

- Ultra small mold type
- Low forward voltage
- High reliability

PINNING

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | Cathode |
| 2 | Anode |

Top View
Marking Code: "Z"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Repetitive Peak Reverse Voltage | $\mathrm{V}_{\mathrm{RM}}$ | 45 | V |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 40 | V |
| Mean Rectifying Current | $\mathrm{I}_{\mathrm{O}}$ | 200 | mA |
| Peak Forward Surge Current (60Hz for Cyc.) | $\mathrm{I}_{\text {FSM }}$ | 1 | A |
| Junction Temperature | $\mathrm{T}_{\mathrm{j}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\mathrm{s}}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Min. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Forward Voltage |  |  |  |  |
| at $I_{F}=10 \mathrm{~mA}$ | $\mathrm{~V}_{\mathrm{F}}$ | 0.16 | 0.3 |  |
| at $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA}$ |  | 0.31 | 0.45 | V |
| at $\mathrm{I}_{\mathrm{F}}=200 \mathrm{~mA}$ |  | 0.41 | 0.54 |  |
| Reverse Current |  |  |  |  |
| at $\mathrm{V}_{\mathrm{R}}=10 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ | - | 20 | $\mu \mathrm{~A}$ |
| at $\mathrm{V}_{\mathrm{R}}=40 \mathrm{~V}$ |  | - | 90 |  |










## PACKAGE OUTLINE



| UNIT | A | $\mathrm{b}_{\mathrm{p}}$ | C | D | E | $\mathrm{H}_{\mathrm{E}}$ | V | $\angle$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | 0.70 | 0.4 | 0.135 | 1.25 | 0.85 | 1.7 | 0.1 | $5^{\circ}$ |
|  | 0.60 | 0.3 | 0.127 | 1.15 | 0.75 | 1.5 |  |  |

